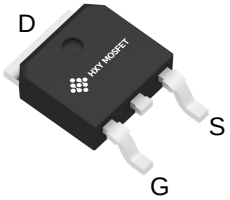
HUF76609D3ST

N-Channel Enhancement Mode MOSFET

Description

The HUF76609D3ST uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.



TO-252-2L

General Features

V_{DS} = 100V,I_D = 10A

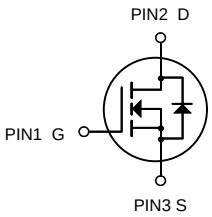
$R_{DS(ON)}$ <160mΩ @ V_{GS}=10V

$R_{DS(ON)}$ <170mΩ @ V_{GS}=4.5V

High density cell design for ultra low Rdson

Fully characterized avalanche voltage and current

Excellent package for good heat dissipation



N-Channel MOSFET

Application

Power switching application

Hard switched and high frequency circuits

Uninterruptible power supply

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HUF76609D3ST	TO-252-2L	HXYMOSFET	2500

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	10	A
Drain Current-Pulsed	I_{DM}	20	A
Maximum Power Dissipation	P_D	40	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	°C
Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	3.75	°C/W

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V,V_{DS}=0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.0		2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=3A	-	140	160	mΩ
		V_{GS}=4.5V, I_D=3A	-	160	170	
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=3A	-	5	-	S
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz	-	650	-	PF
Output Capacitance	C_{oss}		-	25	-	PF
Reverse Transfer Capacitance	C_{rss}		-	20	-	PF
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=50V, R_L=19Ω V_{GS}=10V,R_G=3Ω	-	6	-	nS
Turn-on Rise Time	t_r		-	4	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	20	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	V_{DS}=50V,I_D=3A, V_{GS}=10V	-	20.6		nC
Gate-Source Charge	Q_{gs}		-	2.1	-	nC
Gate-Drain Charge	Q_{gd}		-	3.3	-	nC
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=3A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	7	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics (Curves)

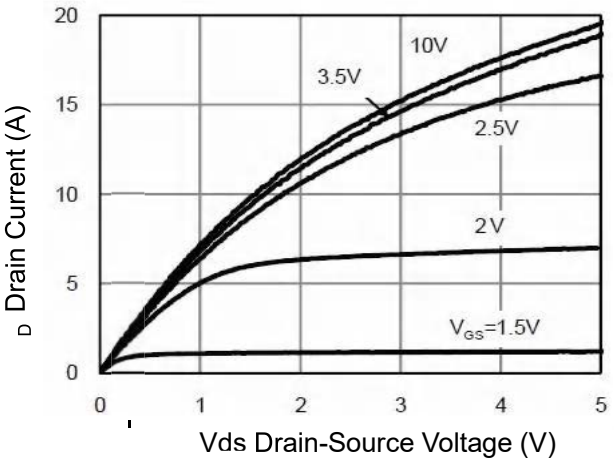


Figure 1 Output Characteristics

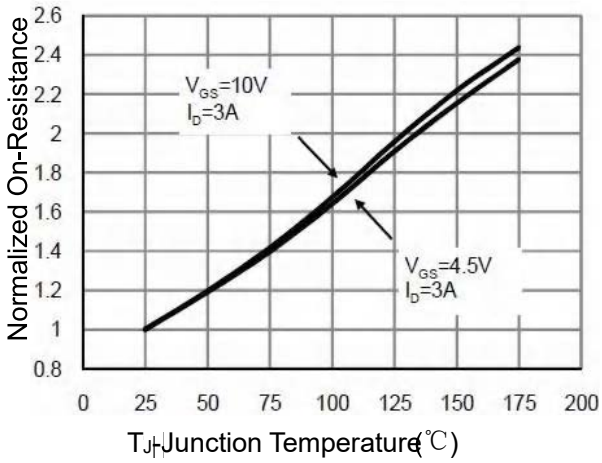


Figure 4 Rdson-Junction Temperature

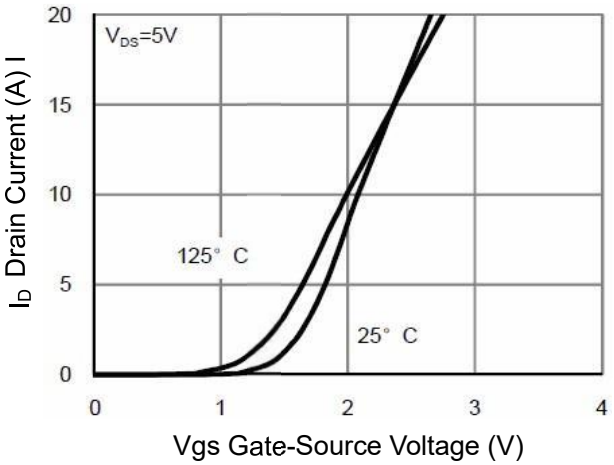


Figure 2 Transfer Characteristics

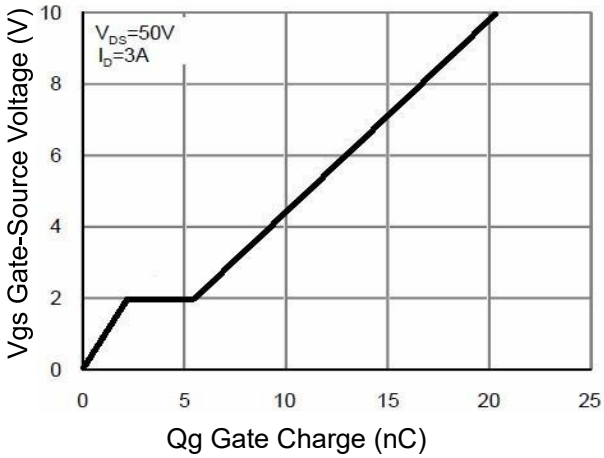


Figure 5 Gate Charge

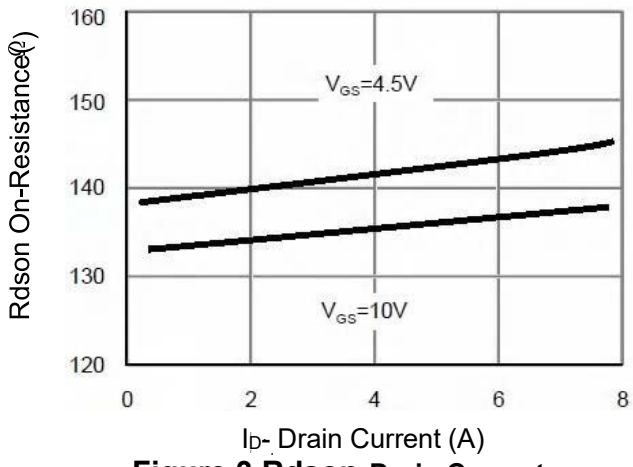


Figure 3 Rdson-Drain Current

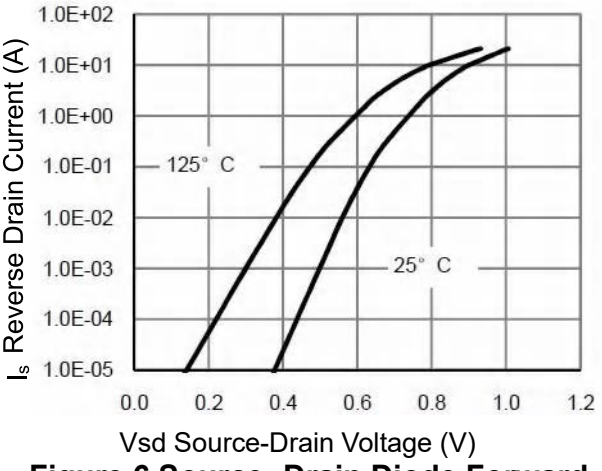


Figure 6 Source- Drain Diode Forward

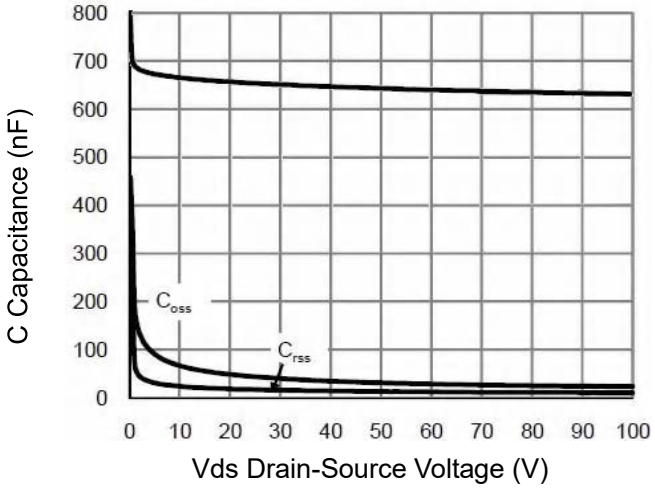


Figure 7 Capacitance vs Vds

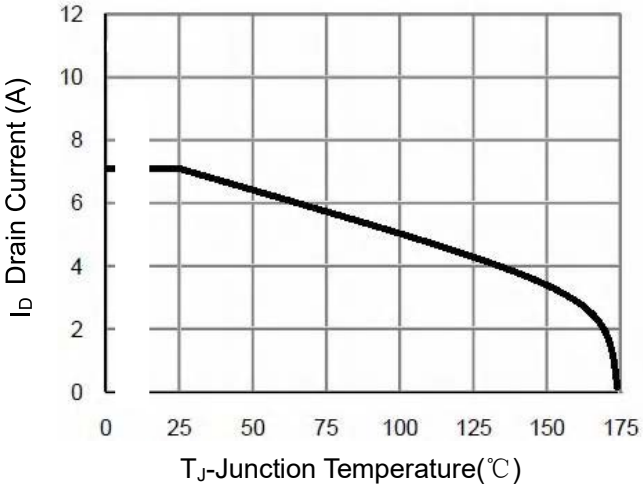


Figure 9 BV_{DSS} vs Junction Temperature

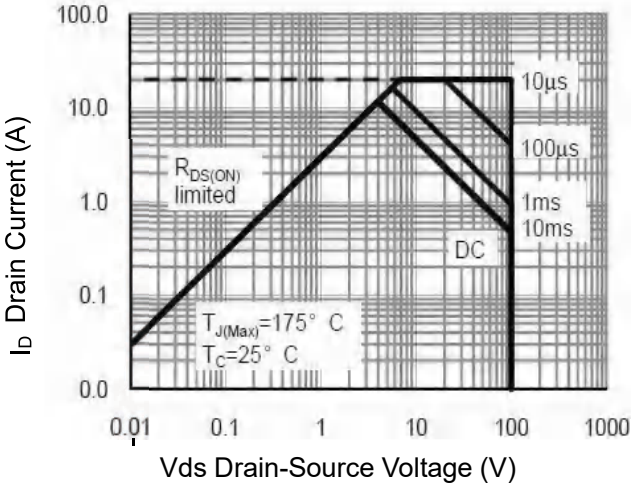


Figure 8 Safe Operation Area

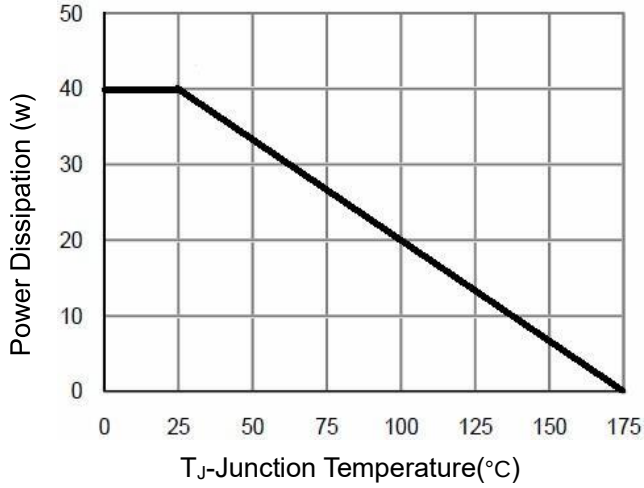


Figure 10 Power De-rating

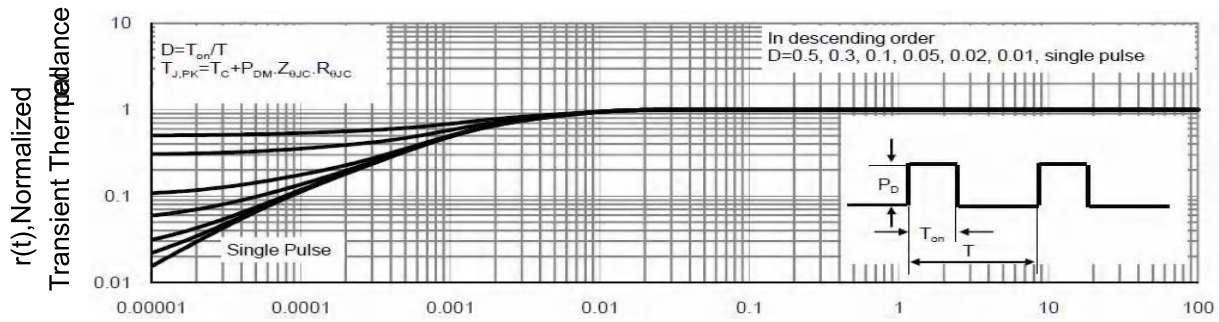
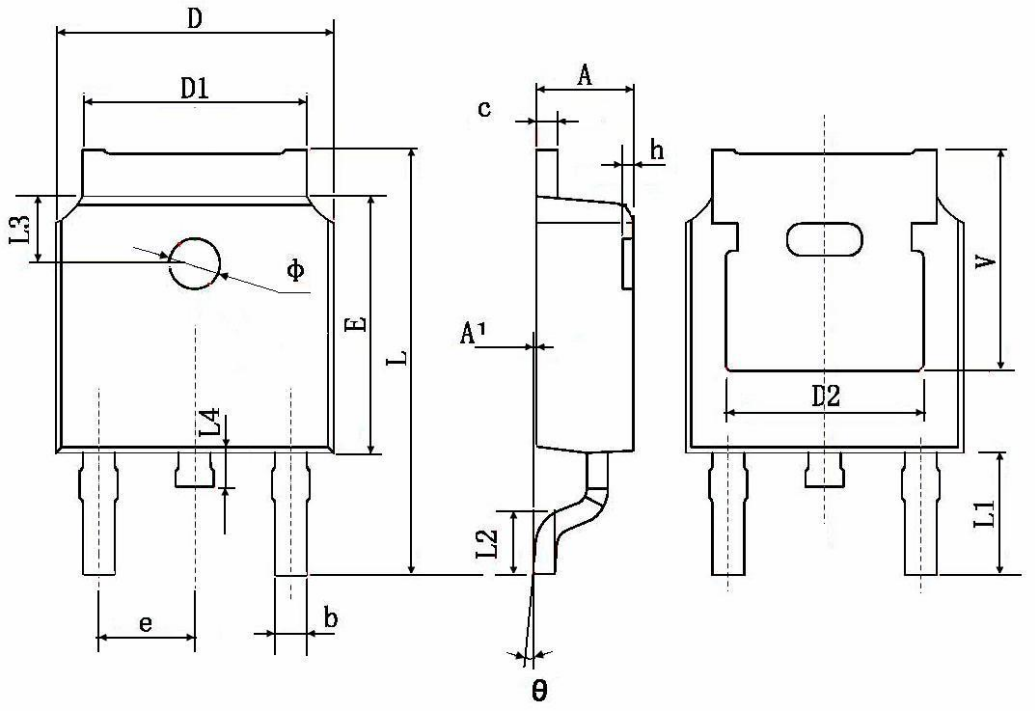


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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